# 3D Monte Carlo simulation of backscattered electron signal variation across pore-solid boundaries in cement-based materials

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#### 6 Abstract

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7 Three-dimensional (3D) Monte Carlo simulation was used to study the variation of backscattered electron (BSE) signal across pore-solid boundaries in cement-based materials in order to enhance quantitative analysis of pore structure. The 8 effects of pore size, depth and boundary inclination angle were investigated. It is found that pores down to 1 nm can 9 10 generate sufficient contrast to be detected. Visibility improves with larger pore size, smaller beam probe size and lower acceleration voltage. However, pixels in shallow pores or near pore boundaries display higher grey values (brightness) 11 than expected due to sampling sub-surface or neighbouring solid material. Thus, cement-based materials may appear 12 13 less porous or the pores appear smaller than they actually are in BSE images. Simulated BSE images were used to test 14 the accuracy of the Overflow pore segmentation method. Results show the method is generally valid and gives low 15 errors for pores that are 1 µm and greater.

Keywords: Backscattered electron imaging; Pore structure; Cement-based materials; 3D Monte Carlo simulation;
 Image analysis; Pore segmentation.

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### 19 **1** Introduction

The microstructure of cement-based materials plays a critical role in controlling the performance of concrete structures. In particular, the pores (and cracks) inherent in the microstructure influences the durability of concrete structures as they provide channels for ingress of deleterious species (such as chloride ions, carbon dioxide, sulphate ions etc.) causing a range of degradation mechanisms. The pore structure, which ranges over six orders of magnitude from nanometre to millimetre, also controls strength, elasticity and other important engineering properties such as creep and shrinkage. As such, there is a huge interest in characterising the pore structure of concrete.

26 Backscattered electron (BSE) microscopy has long been established as a versatile technique for quantitative 27 characterisation of concrete microstructure. This is because the technique is capable of providing actual images of the 28 microstructure at very high resolution and allows different phases to be distinguished based on their brightness [1]. 29 Phase brightness is a function of the collected BSE coefficient, which increases monotonically with mean atomic 30 number of the phase. Hence, in a BSE image of epoxy-impregnated polished cement paste, the unreacted cement 31 particles appear the brightest, followed by hydration products such as calcium hydroxide (CH) and calcium silicate 32 hydrate (C-S-H), while the epoxy-filled pores and cracks appear the darkest. Some applications of quantitative BSE 33 imaging in cement and concrete research include measuring reaction degrees, estimating mix composition and assessing 34 deterioration. Quantitative BSE microscopy has also been used to characterise many other types of porous materials 35 including bone [2], rocks [3] and alloys [4].

36 Two critical aspects of quantitative microscopy are the accuracy of feature segmentation and resolution, i.e. the smallest feature that can be reliably measured. Segmentation is usually carried out by selecting the appropriate upper and lower 37 38 grey level threshold values from the brightness histogram that correspond to the phase of interest. However, the process 39 can be ambiguous and prone to error [5]. This is partly because pixels near boundaries tend to exhibit gradual transition 40 in grey values due to mixing of signals from neighbouring phases. As a result, different phases may share similar grey 41 values making it very difficult to define the thresholds that can satisfy all boundary conditions. In quantitative 42 microscopy, it also important to know the size of the smallest feature that can be reliably imaged and measured. This 43 not only defines the capability of a particular instrument/technique, but also the accuracy and potential errors of the 44 measurement. Furthermore, understanding factors that influence resolution helps optimisation of the imaging technique 45 for a particular application.

46 Monte Carlo simulation of electron-solid interactions offers a unique means to study signal transition across phase 47 boundaries [6, 7] where experiments would not be possible. Such simulations could help improve image segmentation 48 and establish the theoretical resolution for a particular phase of interest. The Monte Carlo technique uses a stochastic 49 process to simulate the elastic and inelastic scattering of electrons in any solids and across any boundary types. Each 450 electron trajectory is monitored in a stepwise manner from its entry point until the electron is either absorbed by the

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- 51 sample or backscattered. This technique has been developed over the last five decades to provide a theoretical
- 52 foundation underpinning electron microscopy and X-ray microanalysis, and to assist quantitative interpretation of SEM
- 53 images. Details of the physics behind the technique can be found in [8] and [9].

In cement and concrete research, Wong and Buenfeld [10] have carried out Monte Carlo simulations to study the shape and size of the interaction volume, spatial and energy distribution of backscattered electrons and characteristic X-rays in cement-based materials. However, the study was limited to two-dimensional simulations of single phases and to tungsten thermionic emitters that have now been surpassed by field emitters. In this paper, we present three-dimensional Monte Carlo simulations to investigate how BSE signal varies across pore-solid boundaries in cement-based materials. A range of pore size, depth and orientation were simulated. Other variables included emitter type, beam accelerating voltage and probe diameter. The aim of the work was to better understand signal transition across pore-solid boundaries

- 61 in order to enhance quantitative analysis of pore structure. Results were used to establish the resolution of BSE
- 62 microscopy for pore analysis and to test accuracy of the Overflow pore segmentation method [11].
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## 64 2 Simulation

#### 2.1 3D Monte Carlo simulation

66 3D CASINO (Version 3.2) was used to perform the simulations throughout this study. The Monte Carlo simulation software is an update of the 2D version developed by [12] and [13]. A comprehensive description of the software is 67 68 given in [14]. In the current version, electron trajectories can be traced in three-dimensions in complicated models built from basic shapes and planes. This allows pore structure of different configurations to be investigated. Another 69 70 important feature is the ability to perform areal scanning to generate realistic BSE images. This is particularly useful for 71 testing and verifying quantitative image analysis. The software allows users to choose various simulation settings 72 including the physical model, number of electrons, angle of incident beam, accelerating voltage, probe diameter etc. 73 Furthermore, the accuracy of the software has been validated by [14] based on a comparison between simulated and 74 measured backscattered coefficients of a silicon sample at beam energies below 5 keV.

75 In this study, the Mott model and the modified Bethe equation were adopted for modelling elastic scattering, and 76 deceleration and energy loss of electrons respectively. In order to ensure that the obtained results were statistically 77 significant, a large number of electrons was simulated per analysis. Unless otherwise stated,  $4 \times 10^5$  electrons were simulated per spot for point and line scans. This yields a relative error of 0.16% ( $\approx 1/n^{0.5}$ , where *n* is the number of 78 79 electrons). For areal scans, the number of electrons was halved to  $2 \times 10^5$  per spot to reduce computation time, but still 80 keeping a small relative error of 0.22%. The computational time for a typical simulation consisting of 124 points using 81 4×10<sup>5</sup> electrons at 10 keV was approximately 5.5 h on a workstation (Intel® Xeon® CPU E5-1650, 3.2 GHz processor). The angle of the incident beam was set perpendicular to the sample surface since this is the most common configuration 82 83 for quantitative BSE imaging. The trajectory of each electron was traced until its energy fell below 50 eV or until it left 84 the sample surface. The probe diameters used and their corresponding accelerating voltages are presented in the following Section. 85

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#### 2.2 Probe diameter

Four different types of emitter were simulated in this investigation to cover the range of emitters available in practice. These were tungsten and lanthanum hexaboride thermionic, Schottky and cold field emitters. The probe diameter for each emitter was derived based on the method proposed by [15]. The method uses practical brightness, which determines the actual amount of current in the probe, to calculate the source image size  $(d_I)$ . The total probe diameter  $(d_P)$  was obtained by adding d<sub>I</sub> together with other contributions including diffraction  $(d_A)$ , chromatic  $(d_C)$  and spherical  $(d_S)$  aberrations using the root-power-sum (RPS) method as shown in Eq. (1). In order to eliminate assumptions concerning the electron probe profile, the full width median (FW50) values were adopted for all contributions. Further

95 explanations of this are given by [15].

$$d_{p} = \sqrt{\left[\left(d_{A}^{4} + d_{S}^{4}\right)^{1.3/4} + d_{I}^{1.3}\right]^{2/1.3} + d_{C}^{2}}$$
 Eq. (1)

Table 1 shows the calculated probe diameters for all emitters at increasing beam energies of 5, 10, 15, 20, 25 and 30
keV. The calculated probe diameters ranged between 1 and 150 nm, and decreased with increasing beam energy as
expected. Field emitters produced the brightest source and smallest probe diameters. Detailed calculations and
assumptions involved are presented in Appendix I.

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#### 102 2.3 3D models of pore-solid boundaries in cement-based materials

103 A total of 119 simulations representing a range of pore sizes and geometries were carried out. The pores were assumed 104 to be filled with a low viscosity araldite resin ( $C_{10}H_{18}O_4$ ) of 1.14 g/cm<sup>3</sup> specific gravity. This is because samples are

- 105 usually impregnated with resin to preserve the delicate microstructure and produce atomic contrast for BSE imaging.
- 106 Calcium silicate hydrate (C-S-H) was taken to represent the solid since this is the main binding phase and hydration
- 107 product forming in the originally water-filled spaces during cement hydration. However, simulating the C-S-H phase is
- 108 challenging because it has variable composition and disordered structure [16-19]. For simplicity, the general formula
- xCaO.SiO<sub>2.y</sub>H<sub>2</sub>O was used. The Ca/Si ratio of C-S-H in hardened cement pastes generally range between 1.2 and 2.3,
- with the mean value close to 1.75 [17]. The H<sub>2</sub>O/SiO<sub>2</sub> ratio and C-S-H density depend on moisture state. However, high-resolution BSE imaging is usually performed on dried samples in vacuum. For C-S-H with a monolayer of water at
- 112 11% relative humidity, an approximated chemical composition of 1.7CaO.SiO<sub>2</sub>.2.1H<sub>2</sub>O and specific gravity of 2.47
- $g/cm^3$  have been suggested [19]. These values were used throughout the study and it is assumed that the variation in
- 114 electron scattering characteristics and the resulting BSE signals within various forms of C-S-H is small and insignificant
- 115 compared to the variation across the pore-solid boundary.

3D models of three basic pore-solid configurations were generated for the simulations (Figure 1). The first model (A) consists of a vertical pore (epoxy-filled) intercalated between two C-S-H blocks of indefinite size. The pore size (*x*) was varied from 1 nm to 10 μm to cover the range of "gel" and "capillary" pores in cement-based materials. This model was used to study the effect of pore size on BSE signal variation and to determine the smallest resolvable pore in BSE imaging. The second model (B) consists of two configurations: a pore overlying a C-S-H layer and another in the reverse order. The thickness of the top layer (*y*) was increased gradually from 0 to 8 μm to investigate the effect of pore depth and sampling of subsurface material on the recorded BSE signal. The third model (C) comprises of adjoining pore

and C-S-H layers inclined at angle  $\theta$  ranging from 10° to 170°. This was used to study how inclination angle of the poresolid boundary affects the transition of BSE signal.

The size of all three models was set to be at least ten times larger than the interaction volume of the electrons to ensure that all interactions occurred within the model and all backscattered electrons were captured. It was assumed that the sample surface was perfectly flat, each phase was stoichiometric and homogeneous, and the interface between the pore and C-S-H phases was abrupt.

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## 130 **3 Results**

## 131 *3.1 Effect of pore size on BSE signal variation*

Figure 2 shows the variation in the simulated BSE coefficient obtained by line scans across the Model A shown in Figure 1. Simulations were carried out for pore sizes of 1 nm, 10 nm, 100 nm, 1 $\mu$ m and 10  $\mu$ m, at 10 and 20 keV beam energies for five emitter types based on the data shown in Table 1. Note that the extent of all scans (linear dimension) was at least ±5× the pore size from the centre of the pore to reduce sample edge effects. The spacing between each scan point (i.e. pixel spacing) was set to be one tenth of the pore size to ensure that sufficient information was captured.

Overall, the amount of BSE signal variation across the pore-solid boundary increases with increase in pore size. The 137 138 BSE coefficient of the pore decreases with increase in pore size and only achieves the correct value for pure epoxy (~0.045-0.047) when the pore size is 100 nm or greater. This is because of the large sampling volume of BSE relative to 139 140 the pore size causing the recorded signals from small pores to be affected by adjacent C-S-H. This effect increases with acceleration voltage. For example, the maximum penetration depth and escape radius of BSE in pure epoxy (average of 141 142 five simulations) are 1.0 and 1.9 um respectively at 10 keV and 3.4 and 6.6 um respectively at 20 keV (Figure 3a). In C-143 S-H, these values are 0.6 and 1.0 µm respectively at 10 keV and 1.8 and 3.6 µm respectively at 20 keV (Figure 3b). The 144 interaction volume of electrons in epoxy is almost  $3.5 \times$  larger than in C-S-H as the mean atomic number of epoxy 145 (6.184) is much lower than that of C-S-H (12.086) [10].

146 For a 1 nm pore, the field emitters are able to detect a slight signal variation across the pore whereas the thermionic emitters detect no signal variation. This is simply because the thermionic emitters have probe diameters much larger 147 148 than the pore thus a large proportion of the incident electrons enter and backscatter directly from the C-S-H. For 10 nm 149 and 100 nm pores, all emitters show improvements in the detected signals, but significant differences between the 150 performance of field and thermionic emitters are still evident. At 1 um and above, all emitters show similar levels of 151 BSE signal variation. It is also noted that transition of the BSE coefficient is not abrupt, but occurs over a finite distance 152 (up to 500 nm in some cases) as the beam scans across the pore-solid boundary. For large pores, there is a slight increase in the BSE signal on the C-S-H side as the beam approaches the pore-solid boundary. This is an edge effect 153 154 due to strong scattering of electrons from the high atomic C-S-H into the low atomic epoxy-filled pore that 155 consequently has greater probability of escaping the sample. An opposite effect occurs on the pore side of the boundary causing a slight dip in the BSE signal. 156

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## 158 *3.2 Contrast and visibility of pores*

Since the BSE signal variation decreases with decrease in pore size, there will be a limit when the signal variation is too small to be discernable. This would represent the spatial resolution or detection limit for imaging pores. One useful way to quantify the visibility of the pore is to calculate the contrast between the pore and adjacent C-S-H using Eq. (2).

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$$C = \frac{\eta_1 - \eta_2}{\eta_1} \times 100, \eta_1 > \eta_2$$
 Eq. (2)

163 Where  $\eta_1$  and  $\eta_2$  are the BSE coefficients of the C-S-H and at the centre of the pore respectively.

Figure 4 (a) and (b) show the calculated BSE contrast as a function of the pore size and probe diameter respectively.

165 The signal contrast increases with increase in pore size, but reduces with increasing probe diameter (when the pore size 166 is smaller than the probe diameter). The theoretical contrasts between pure epoxy ( $\eta_2 \sim 0.045 - 0.047$ ) and pure C-S-H

167  $(\eta_1 \sim 0.142 - 0.143)$  at 10 and 20 keV are approximately 67% and 68% respectively. Such levels of contrast are only

observed in the simulations for pores 100 nm or greater at 10 keV (1000 nm at 20 keV). As expected, the contrast at 20

169 keV is lower than at 10 keV. The contrast peak at 1000 nm is likely to be due to the drop in BSE signal at the centre of 170 the pore caused by edge effects at the boundaries. Assuming that the minimum contrast required for visibility is 5% [9],

171 the simulations suggest that a pore as small as 10 nm (1 nm in some cases) can generate sufficient contrast to be

- detected. This is true despite the fact that the pore size is substantially smaller than the BSE sampling volume (Figure
- 173 3).

174 Figure 5 shows the simulated BSE images for Model A to study the effect of pore size, emitter type and beam energy on 175 visibility. The simulated BSE coefficients were converted into grey values that stretch across the 8-bit grey scale (0 to 255) using the mat2gray and im2uint8 functions in MATLAB®. A grey value of "0" represents the BSE coefficient of 176 177 pure epoxy whereas a grey value of "255" represents the BSE coefficient of tetracalcium aluminoferrite (C<sub>4</sub>AF), which 178 is the brightest phase present in unreacted cement in hardened cement paste. This was to give the simulated pore and C-179 S-H phases grey values that resemble those from real BSE images of cement paste. The pixel spacing is one tenth of the 180 pore size and the image size is  $100 \times 25$  pixels; the total pore fractions in all images are therefore exactly 10%. There 181 are a few interesting observations to be made from these figures. First, in agreement with the results in Figure 2 and 4, a pore size as small as 1 nm is indeed detectable with field emitters; however, its visibility is poor. Second, the boundary 182 between pore and C-S-H appears fuzzy for pores smaller than the probe diameter. Third, the contrast between pore and 183 184 C-S-H is noticeably higher at 10 keV than at 20 keV. Overall, as already discussed above, these conditions improve 185 with increasing pore size and decreasing probe diameter and accelerating voltage. From the following section onwards, all simulations were performed using the Schottky field emitter since it is a commonly used emitter in modern SEMs 186 and offers good resolution. 187

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#### 189 *3.3 Effect of sampling subsurface material*

Figure 6 (a) shows the change in BSE coefficient as the thickness (depth) of the epoxy-filled pore layer overlying the CS-H layer (Model B, Figure 1) increases from 0 to 7 µm. Figure 6 (b) shows the results for the reverse configuration (CS-H layer overlying pore). The accelerating voltage was increased from 5 to 30 keV at 5 keV intervals to investigate the
effect of the interaction volume on sampling subsurface material. The simulated BSE coefficient has a marginal
dependency on accelerating voltage. This is a well-known phenomenon, but the exact relationship between the BSE
signal and accelerating voltage is complex. However, the variation in the BSE coefficient within the accelerating
voltage range of 5 to 50 keV is generally less than 10% [9].

197 Results for both configurations demonstrate that when the thickness of the top layer decreased beyond a critical value, the BSE coefficient changes gradually to that of the bottom layer material. This is because the electron beam penetrates 198 199 the top layer and samples the bottom layer. This critical thickness is approximately the maximum penetration depth of 200 the backscattered electrons of the top layer. The resulting BSE pixel brightness is therefore not that of the top layer. As expected, the critical thickness increases with accelerating voltage. For a pore/C-S-H configuration, the critical 201 thickness range from 0.3 µm at 5 keV to 6.6 µm at 30 keV. For a C-S-H/pore configuration, the critical thickness ranges 202 203 from 0.2 µm at 5 keV to 3.2 µm at 30 keV. Unsurprisingly, the critical thickness is larger when the pore is overlying C-204 S-H.

205 Figure 7 shows simulated BSE images of an epoxy-filled pore that is overlying C-S-H at 10 and 20 keV. The images are 206  $10 \times 10$  pixels at 0.1 µm spacing. The simulated BSE coefficients were converted to pixel grey values and stretched across the 8-bit grey scale (see Section 3.2 for explanation). Results show that the grey value of a pore can spread over a 207 208 range depending on its depth due to sampling of underlying C-S-H. Pores shallower than the critical thickness would 209 share similar grey value as the solid C-S-H. The opposite effect could occur if a thin C-S-H layer overlies a large pore, 210 but this is expected to be less severe because the penetration depth of BSE in C-S-H is less than half of that in epoxy. 211 The implication of this is that cement-based materials with very fine pore sizes would appear to be denser (i.e. having 212 lower porosity) than they are. Pores may appear smaller than they actually are due to the transition in grey value near boundaries. Undoubtedly, this effect increases the ambiguity concerning the true position of the pore-solid boundary, 213 214 creates errors during pore segmentation and limits the smallest pore size that can be reliably imaged.

#### 216 *3.4 Pore-solid boundary inclination angle*

217 In reality, the pore-C-S-H boundaries are not perpendicular to the sample surface, but occur at varying angles because

of their complex and irregular morphology. Figure 8 shows the effect of this on the BSE coefficient measured by line scans across Model C (Figure 1) where the pore-C-S-H boundary angle varied from 10° to 170°. The scans were up to  $\pm$ 20 µm from the pore-C-S-H boundary. The position of the first and last point of each scan was such that their distances to the boundary were greater than the BSE escape surface radius of epoxy and C-S-H respectively. The spacing between each point was 20 nm at 10 keV and 100 nm at 20 keV.

Figures 9 (a), (b) and (c) show the change in the shape and size of the interaction volume of electrons across the pore-C-

S-H boundary at 10°, 90° and 170° respectively at 10 keV. As the incident beam approaches the boundary, electrons

begin to sample the neighbouring higher atomic number C-S-H phase and the interaction volume diminishes in size. The changes in size and shape of the interaction volume, and in the resulting BSE coefficients are more abrupt when the

boundary is perpendicular to the surface, but occur more gradually with shallow sloping boundaries (10° and 170°) due

228 to sampling of subsurface material. This effect is more severe on the pore phase where the BSE signal transition can occur over a distance of 5 µm at 10 keV and 16 µm at 20 keV for a 10° slope (Figure 8).

Figure 10 shows the simulated BSE images of pore-C-S-H boundaries at various inclination angles at 10 keV. The image size is  $1800 \times 120$  pixels at 0.1 µm spacing. The pore fraction in all images is 50%. It can be seen that the pixels near sloping boundaries exhibit a gradient in grey value and that the effect is stronger on the pore phase. This clearly presents a significant challenge in determining the true position of the pore-C-S-H boundary. In manual thresholding, one is likely to assume that the darkest pixels represent the pore phase. This would under-estimate the size of pores at angles < 90° and over-estimate at angles > 90°.

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#### 3.5 Pore segmentation via image analysis

238 As mentioned in the Introduction, one of the main motivations for this study was to test the accuracy of the Overflow 239 method [11] for segmenting pores in cement-based materials. The simulated BSE images in the previous sections serve 240 as a useful tool for this purpose. In the Overflow segmentation method, the upper threshold grey value for pores is 241 determined from the inflection point in the cumulative brightness histogram of the BSE image. This represents a critical 242 point at which the segmented pore areas start to 'overflow' into the surrounding solid paste matrix. The method provides a consistent means for phase segmentation and it has since been used in a number of applications including 243 244 clinker studies [20], characterising microstructure development and interfaces [21-25], determining original 245 water/cement ratio and mix composition [26], and mass transport modelling [27, 28].

Figure 11 shows the cumulative brightness histograms of the simulated BSE images from Sections 3.1 & 3.2 (from Figure 5). It can be seen that the simulated curves exhibit a sigmoidal behaviour similar to those from real BSE images of cement-based materials. The sigmoidal trend increases with increase in contrast and sharpness of the pore-solid boundary. Note that the results from a 1 nm pore obtained by the tungsten and lanthanum hexaboride emitters, and from a 10 nm pore obtained by the tungsten emitter were excluded from the analysis as these images do not contain sufficient signal to resolve the pore phase (Figure 5).

252 The inflection points determined by the Overflow method are marked with crosses while the correct grey values that 253 correspond to the exact pore area fractions are marked with circles. The results show that when pores are smaller than 1 254  $\mu$ m, the inflection points overestimate the correct grey values with significant errors. Note that these errors are not due 255 to digitisation effects since the pixel size in the simulations were set at one-tenth of the pore size. For pores of 1 µm and 256 greater, the inflection points generally agree very well with the correct grey values (Figure 11 d and e) in particular for 257 field emitters at 10 keV. Figure 12 compares the overflow segmented pore size with the actual pore size. It can be seen that the agreement between measured and actual values improves with increase in pore size. For pores of 1 µm and 258 259 greater, errors of  $\sim 1\%$  were observed for field emitters at 10 keV. The results suggest that the minimum pore size that 260 can be accurately segmented by the Overflow method is approximately half the BSE escape radius in epoxy, which is 1 261 µm and 3 µm at 10 keV and 20 keV respectively for field emitters.

262 Figure 13 shows the cumulative brightness histograms and pore segmentation errors for the simulated images from 263 Section 3.4 (from Figure 10) with inclined pore-solid boundaries. The segmentation is very accurate for pores with < 264 90° inclination angles. However, segmentation errors increase for inclination angles larger than 90°, up to a value of 265 30.7% at 170°. The over-estimation is due to presence of dark pixels on the C-S-H side of the boundary from sampling 266 subsurface pore (Figures 9c & 10). Assuming that pores are randomly orientated and that the probability of the pore 267 occurring at any angle is equal, the error contribution from each inclination angle can be averaged to determine the 268 overall percentage error of the segmentation. The resulting value is 5.2% and this indicates that the total pore fraction 269 would be marginally overestimated with the Overflow method.

## 271 4 Discussion

272 Electron scattering near phase boundaries is a complex process. This is particularly true if the phases have large

differences in atomic number and density since the interaction volume from which useful signals emerge will vary on both sides of the interface. Near boundaries, scattered electrons can move from one phase to another and this influences the collected signals and images. For BSE imaging of cement-based materials, samples are usually impregnated with a

275 the confected signals and images. For BSE imaging of cement-based materials, samples are usually impregnated with low atomic number material (epoxy) to generate high contrast between pores (or cracks) and solids. This enhances

277 visibility and facilitates quantitative characterisation via image analysis.

278 However, the large interaction volume in epoxy-filled pores increases the likelihood of sampling sub-surface or 279 neighbouring solid phases. This can be problematic because the pores (gel and capillary) in cement-based materials 280 range from sub-micron to several microns in size and the pore boundaries with solid hydration products have complex morphologies. This study shows that the signal measured across pore boundaries may vary over a distance of several 281 microns. Pixels in shallow pores or near boundaries will display grey values (brightness) higher than expected because 282 of additional scattering events occurring into the solid hydration products. This adds uncertainty concerning the exact 283 284 location of the pore-solid boundary for segmentation and image analysis. It also means that the sample may appear less 285 porous or the pores appear smaller than they actually are in BSE images.

As shown in this study, the spatial resolution of BSE imaging for pore characterisation is influenced by the probe size, signal sampling volume and interactions that occur near phase boundaries. These are dependent on the emitter type, beam energy and composition of the phases present. The fact that pores smaller than the BSE sampling volume or the electron probe size are visible (Figure 5) shows that these dimensions do not represent the spatial resolution limit. This is because phase visibility depends on the difference between the BSE signal detected from that particular phase and its neighbouring region, i.e. contrast. Features smaller than the BSE sampling volume or probe size can still be detected as long as the obtained contrast satisfies the visibility criteria.

293 Since the collected images are digitised, the pixel size may also influence final resolution. Pixel size decreases with

increase in magnification. For images captured at low magnification, spatial resolution is likely to be limited by the pixel size. However, at high magnification, the influence of pixel size becomes less important especially when it is

296 much smaller than the signal sampling volume or the electron probe diameter. This is because of overlapping signals

- from adjacent pixels. Therefore, pixel size is not always equivalent to the image resolution. The actual resolution can be no better than the pixel size, but is generally less due to the various factors discussed above.
- 299 It is important to note that the results presented in this paper represent ideal imaging conditions. In reality, the spatial 300 resolution could be worse. This is because the effect of noise was not considered in the simulations. Signal noise can 301 come from uneven surface topology and geometry of the sample, poor efficiency of the detector, shot noise from the 302 electron beam, insufficient number of electrons collected due to high scan speed, inadequate imaging environment and 303 signal digitisation process etc. These factors will further complicate the BSE signal generation across the pore-C-S-H 304 boundary. In real cement-based materials, pores can also occur adjacent to other solid phases such as calcium hydroxide 305 (CH) and unreacted cement phases. In particular, 'Hadley' grains, which consist of darker rims (mixture of porosity and 306 low-density C-S-H) around unreacted cement, can often be present in the microstructure of cement paste [29-31]. Both CH and unreacted cement have higher atomic number than C-S-H and would increase the BSE coefficient at the pore 307

boundary. However, the general behaviour of the signal transition across the pore boundary should be similar to that

309 observed in this study.

Although pores smaller than the BSE sampling volume or the electron probe size may be visible (Figure 5), significant measurement errors could occur during quantitative image analysis. The magnitude of this error would depend on the

size of the pore with respect to the image resolution and the accuracy of the segmentation method employed.

313 Segmentation is one of the most important, but error prone, processes in quantitative microscopy. The Overflow

segmentation method was shown to be accurate for segmenting pores that are larger than half the escape radius of

- backscattered electrons. The Overflow method is also able to determine the boundary of shallow pores overlying C-S-H
- and inclined pores with reasonably low errors. Thus, the method seems robust and handles grey scale variation at pore-

317 solid boundaries well. Nevertheless, it has to be stressed that no segmentation method is perfect and that some degree of 318 error will always occur during image analysis, particularly for heterogeneous, multi-phase and multi-scale materials.

The magnitude and significance of this error should always be considered in quantitative image analysis.

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## 321 5 Conclusion

A 3D Monte Carlo technique was used to study the variation of backscattered electron (BSE) signal across pore-solid (C-S-H) boundaries in cement-based materials. The simulated pores were epoxy-filled and covered a range of sizes (1

 $10^{\circ}$  nm to  $10 \ \mu$ m), depths (0 to 7  $\mu$ m) and inclination angles ( $10^{\circ}$  to  $170^{\circ}$ ). Other variables included emitter type (tungsten

thermionic, LaB<sub>6</sub>, Schottky and tungsten cold field), accelerating voltage (5 to 30 keV) and probe diameter (1 to 150 nm). The main findings area

326 nm). The main findings are:

- a) A pore size of 1 nm can generate sufficient contrast at 10 keV using Schottky or cold field emitters to allow
   detection, despite the pore itself being smaller than the beam interaction volume. However, the visibility of 1 nm
   pores is poor. The visibility improves with increasing pore size, but degrades with increasing probe diameter and
   a) a celerating voltage.
- b) Pores pixels can appear brighter (i.e. having larger grey value) than expected in BSE images due to sampling of sub-surface or neighbouring solid material. This occurs in shallow pores where the depth to underlying solid C-S-H is less than the maximum penetration depth of BSE in epoxy ( $\sim$ 1.0 µm at 10 keV and 3.4 µm at 20 keV). This also occurs when pore pixels are located within the BSE escape radius in epoxy ( $\sim$ 1.9 µm at 10 keV and 6.6 µm at 20 keV) from the boundary.
- c) These effects may cause misinterpretation of BSE images of heterogeneous porous materials. Pores in cement based materials may appear smaller than they actually are due to the transition in grey value near boundaries from
   sampling sub-surface or neighbouring solids. This increases the uncertainty concerning the true position of pore solid boundaries, creates potential errors during segmentation and further limits the smallest pore that can be
   reliably measured.
- d) Monte-Carlo simulated BSE images were used to test the accuracy of the Overflow pore segmentation method.
   Results show that the cumulative brightness histograms of the simulated images exhibit a sigmoidal behaviour
   similar to real BSE images of cement-based materials. The inflection point in the cumulative brightness histogram
   provides a good estimate for the threshold grey value for pore segmentation. For pore sizes of 1 μm and greater,
   the Overflow method gave errors of ~1% with field emitters at 10 keV. For inclined pores with random
   orientation, the average segmentation error was 5.2%.
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 Engineering, Imperial College London.

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#### 426 APPENDIX

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- 427 This section presents the calculations of the probe diameters for the four different emitters used in the study (tungsten
- thermionic (T-W), lanthanum hexaboride thermionic (T-LaB<sub>6</sub>), zirconium oxide/tungsten Schottky field emitter (SFE)
   and tungsten cold field (CFE) emitters). The calculations are based on the method of [15] which introduces the concept
   of practical brightness (B<sub>prac</sub>).
- 431 For thermionic and Schottky emitters:

$$B_{prac} = 1.44 \frac{eJ}{\pi kT}$$
 Eq. (I.1)

433 and for cold field emitters:

$$B_{prac} = 1.44 \frac{eJ}{\pi d}$$
 Eq. (I.2)

where *e* is the elementary electric charge (= $1.60 \times 10^{-19}$  C), *j* (A/m<sup>2</sup>) is the emission current density, *k* is the Boltzmann constant (= $1.38 \times 10^{-23}$  J/K), *T* (K) is the emission temperature and *d* (J) is the mean tangential energy. The emission temperatures for T-W, T-LaB<sub>6</sub> and SFE are taken as 2700, 1700 and 1800 K respectively whereas the emission current density *i* can be calculated using the following equations:

439 For thermionic emitters:

440 
$$J = -\left(\frac{4\pi em}{h^3}\right)kT^2 \exp\left(\frac{-e\phi}{kT}\right)$$
 Eq. (I.3)

441 for Schottky field emitters:

442 
$$J = \frac{em}{2\pi^2 \hbar^3} (kT)^2 \exp\left(-\frac{\phi - \sqrt{\frac{e^3 F}{4\pi\varepsilon_0}}}{kT}\right) \frac{\pi q}{\sin \pi q} \quad \text{, with } q = \frac{\hbar}{\pi kT \sqrt{m}} (4\pi\varepsilon_0 eF^3)^{1/4} \qquad \text{Eq. (I.4)}$$

443

451

444 And for cold field emitters:

445 
$$J = \frac{q^2}{8\pi h\phi} (\beta F)^2 \exp\left(-\frac{\frac{4}{3}\sqrt{\frac{8\pi^2 m}{h^2}} \frac{(q\phi)^{3/2}}{q}}{\beta F}\right)$$
Eq. (I.5)

Where *m* is the mass of electron (=9.11 × 10<sup>-31</sup> kg), *h* is the Planck's constant (=6.63 × 10<sup>-31</sup> Js),  $\phi$  is the work function (=4.5 eV for W, 2.4 eV for LaB<sub>6</sub> and 2.9 eV for ZrO/W),  $\hbar$  is the reduced Planck's constant (=1.05 × 10<sup>-31</sup> Js), *F* is the electric field (taken as 6.5 × 10<sup>8</sup> V/m for SFE and 10 × 10<sup>8</sup> V/m for CFE) and  $\varepsilon_0$  is the permittivity of free space (=8.85 × 10<sup>-12</sup> F/m).  $\beta$  is the field enhancement factor for CFE and it can calculated based on the geometry of the emitter tip using the equation proposed by [32]:

$$\beta = 1 + \sqrt{h/2r} \qquad \qquad \text{Eq. (I.6)}$$

Note that this equation is based on the assumption that the distance between the anode plane and the emitter tip is sufficiently large. Supposing that the height (*h*) and radius (*r*) of the emitter tip are 4000 and 100 nm respectively, the resulting  $\beta$  is equal to 5.47. Following the work of Wong and Buenfeld [10], it is assumed that the microscope is set up to image an atomic number contrast level of 2.5% with a detector collection efficiency of 0.1 and scan time of 100s for

- 456 a  $1024 \times 768$  image. Thus, a probe current ( $I_p$ ) of 0.5 nA is employed. By knowing the practical brightness and the 457 probe current, the full width median (FW50) source image size can be determined as follows:
- 458  $d_I = \sqrt{\frac{4I_p}{\pi^2 \alpha_p^2 V_p B_{prac}}}$  Eq. (I.7)

459 Where  $\alpha_p$  and  $V_p$  are the beam half opening angle at the target (= 0.005 rad) and the accelerating voltage (5 to 30 keV)

460 respectively. The contributions from other sources including diffraction and chromatic and spherical aberrations are

461 calculated using Eq. (I.8-1.10) respectively:

462 
$$d_{A} = \frac{0.66 \times 10^{-9}}{\sqrt{V_{p} \alpha_{p}}}$$
 Eq. (I.8)

463 
$$d_{C} = 0.6C_{C} \frac{\Delta E_{FW50}}{V_{p}}$$
 Eq. (I.9)

$$d_s = 0.18C_s \alpha_p^3 \qquad \qquad \text{Eq. (I.10)}$$

465 Where  $C_c$  (m),  $C_s$  (m) are the chromatic and spherical aberration coefficients respectively and  $\Delta E_{FW50}$  (eV) is the FW50 466 variation in beam voltage. The  $C_c$  and  $C_s$  values for the thermionic emitters, SFE and CFE are taken as 0.01 & 0.02 m, 467 0.0027 & 0.0032 m and 0.0018 & 0.0020 m respectively whereas the  $\Delta E_{FW50}$  for T-W, T-LaB<sub>6</sub>, SFE and CFE are taken 468 as 2, 1, 0.6 and 0.3 eV respectively. The total probe diameter ( $d_p$ ) is then calculated by adding all the contributions 469 together using the root-power-sum (RPS) based equation:

470 
$$d_p = \sqrt{\left[\left(d_A^4 + d_S^4\right)^{1.3/4} + d_I^{1.3}\right]^{2/1.3} + d_C^2}$$
 Eq. (I.11)

## **TABLES & FIGURES**

499 Table 1: Calculated practical brightness (B<sub>prac</sub>), diameter of source image (d<sub>1</sub>), contributions from chromatic (d<sub>C</sub>) and

spherical (ds) aberrations and diffraction (dA), and resulting total probe diameter (dp) for different emitters at increasing
 accelerating voltages (E). W, LaB<sub>6</sub> and ZrO represent tungsten, lanthanum hexaboride and zirconium oxide respectively.

	E (keV)	B <sub>pract</sub> (A/m <sup>2</sup> sr)	dı (nm)	dc (nm)	ds (nm)	d <sub>A</sub> (nm)	d <sub>p</sub> (nm)
Thermionic (W)	5	3.44E+08	153.54	6.80	0.45	1.87	154.07
	10	6.88E+08	108.57	3.40	0.45	1.32	108.89
	15	1.03E+09	88.65	2.27	0.45	1.08	88.90
	20	1.38E+09	76.77	1.70	0.45	0.93	76.98
	25	1.72E+09	68.66	1.36	0.45	0.83	68.85
	30	2.06E+09	62.68	1.13	0.45	0.76	62.85
Thermionic (LaB <sub>6</sub> )	5	4.17E+09	44.09	3.40	0.45	1.87	44.78
	10	8.34E+09	31.18	1.70	0.45	1.32	31.62
	15	1.25E+10	25.46	1.13	0.45	1.08	25.80
	20	1.67E+10	22.05	0.85	0.45	0.93	22.34
	25	2.08E+10	19.72	0.68	0.45	0.83	19.98
	30	2.50E+10	18.00	0.57	0.45	0.76	18.24
Schottky Field Emitter (ZrO/W)	5	2.35E+11	5.88	0.55	0.07	1.87	6.89
	10	4.69E+11	4.16	0.28	0.07	1.32	4.87
	15	7.04E+11	3.39	0.18	0.07	1.08	3.97
	20	9.38E+11	2.94	0.14	0.07	0.93	3.44
	25	1.17E+12	2.63	0.11	0.07	0.83	3.08
	30	1.41E+12	2.40	0.09	0.07	0.76	2.81
Cold Field Emitter (W)	5	3.41E+12	1.54	0.18	0.05	1.87	2.91
	10	6.83E+12	1.09	0.09	0.05	1.32	2.06
	15	1.02E+13	0.89	0.06	0.05	1.08	1.68
	20	1.37E+13	0.77	0.05	0.05	0.93	1.45
	25	1.71E+13	0.69	0.04	0.05	0.83	1.30
	30	2.05E+13	0.63	0.03	0.05	0.76	1.19



Figure 1. Schematics (not to scale) of the generated 3D pore-solid models for studying the effect of (A) pore size, (B) sampling subsurface materials and (C) inclination angle of the pore-solid (C-S-H) boundary on BSE signal. Note that the shaded region represents epoxy-filled pore whereas the unshaded region represents C-S-H. The direction of the electron beam is indicated by the black arrow.

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Figure 2. Variation in BSE coefficient across pore sizes of (a) 1 nm, (b) 10 nm, (c) 100 nm, (d) 1 µm and (e) 10 µm at 10 and 20 keV for different emitters (Model A). The pixel spacing is one tenth of the pore size.



Figure 3. Monte Carlo simulations of electron-solid interactions in (a) pure epoxy and (b) pure C-S-H performed with a Schottky field emitter at 10 and 20 keV. Blue lines represent absorbed electron trajectories whereas red lines represent backscattered electron trajectories. Scale bar is 3 µm.





Figure 4. Calculated BSE contrast from Model A between the pore and C-S-H as a function of (a) pore size and (b) probe diameter at 10 keV (solid line) and 20 keV (dashed line). Values in the legend to (b) are pore size.



Figure 5. Simulated BSE images of pores (Model A) showing the effect of pore size, beam energy and emitter type on visibility of the pore. Pixel size is one-tenth of the pore size and image size is  $100 \times 25$  pixels. Scale bar represents the pore size.



Figure 6. BSE coefficient changes as a function of the thickness of the top layer due to sampling of the bottom layer. Simulations were carried out on Model B for the case of (a) epoxy-filled pore layer overlying C-S-H layer and (b) C-S-H layer overlying epoxy-filled pore layer.



Figure 7. Simulated BSE images of an epoxy-filled pore that is overlying C-S-H. The resultant grey value of the pore varies depending on its thickness (i.e. depth). Grey values of pure epoxy and C-S-H are shown for comparison. Image size is  $10 \times 10$  pixels at 0.1 µm spacing.



Figure 8. Change in BSE coefficient across pore-C-S-H boundaries set at various inclination angles (Model C) at (a) 10 keV and (b) 20 keV.



Figure 9. Change in shape and size of the interaction volume as the beam is scanned across pore-C-S-H boundary set at inclination angles of (a) 10°, (b) 90° and (c) 170° at 10 keV. Note that the dark region represents epoxy-filled pore whereas the bright region represents C-S-H. Scale bar is 1 µm.



Figure 10. Simulated BSE images (10 keV) across pore-C-S-H boundaries at various inclination angles showing grey value transition near boundary. Image size is 1800 × 120 pixels at 0.1 μm spacing. Scale bar is 6 μm.



Figure 11. Cumulative brightness histogram for the simulated BSE images in Sections 3.1 & 3.2 (from Figure 5) at increasing pore size. Crosses mark the inflection point determined by the Overflow segmentation method whereas circles mark the correct grey values that give the actual pore fraction. Note that the scale of the X-axis has been expanded for clarity.



Figure 12. (a) Comparison between the Overflow segmented pore size and the actual pore size; (b) segmentation error vs. pore size.



Figure 13. (a) Cumulative brightness histogram for the simulated BSE images in Section 3.4 (from Figure 10) at increasing pore boundary inclination angle. Crosses mark the inflection point determined by the Overflow segmentation method whereas circles mark the correct grey values that give the actual pore fraction. Note that the scales of the Y and X-axes have been expanded for clarity; (b) segmentation error vs. pore-C-S-H boundary inclination angle.